

30 V, 4.2 A PNP low V_{CEsat} (BISS) transistor Rev. 01 — 1 April 2010

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4032NX.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- Optimized switching time
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-4.2	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-	-10	A
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -4 \text{ A};$ $I_{B} = -400 \text{ mA}$	<u>[1]</u> _	58	86	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter	_	_
2	collector		2
3	base		3
			006aaa231

3. Ordering information

Table 3. Orde	ring inform	ation	
Type number	Package		
	Name	Description	Version
PBSS4032PX	SC-62	plastic surface-mounted package; 3 leads	SOT89

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PBSS4032PX	*6J

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-30	V
V _{CEO}	collector-emitter voltage	open base	-	-30	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-4.2	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-10	А
I _B	base current		-	-1	А

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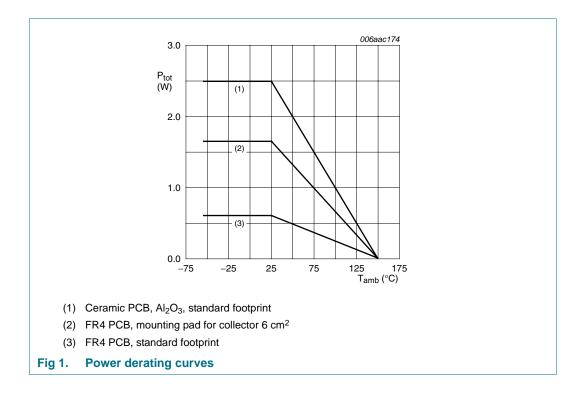
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	P _{tot} total power dissipation	dissipation $T_{amb} \le 25 \text{ °C}$	[1] -	600	mW
			[2] _	1650	mW
			[3] _	2500	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

 Table 5.
 Limiting values ...continued

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



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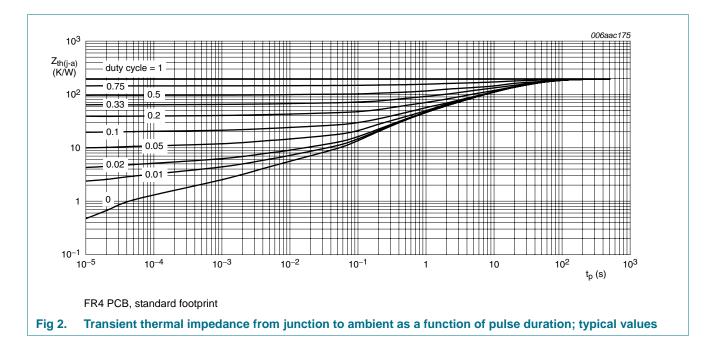
6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	-a) thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	210	K/W
			[2] _	-	75	K/W
			<u>[3]</u> _	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

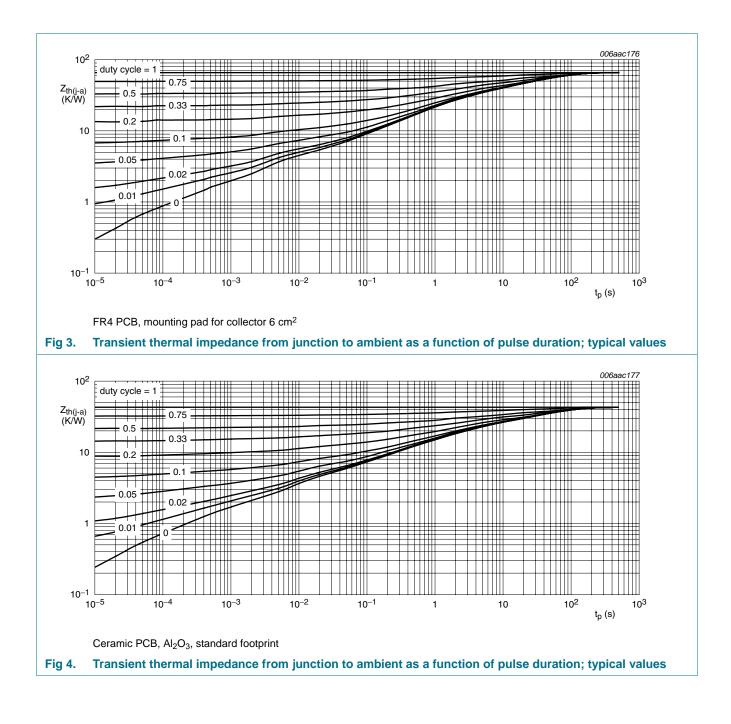


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7. Characteristics

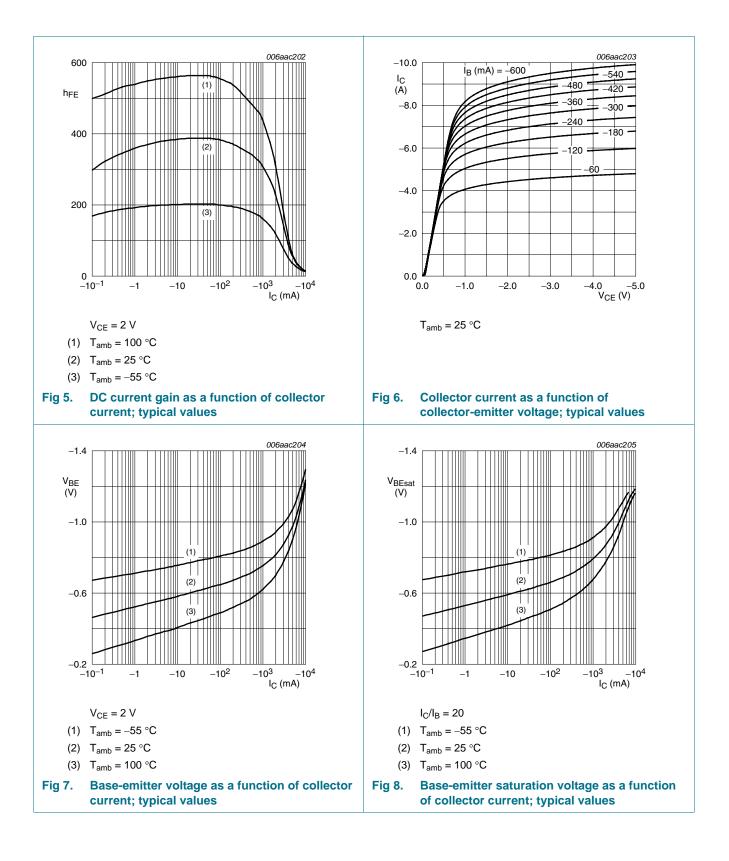
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -30 V; I _E = 0 A		-	-	-100	nA
current		$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ T _j = 150 °C		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -24 \text{ V}; \text{V}_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 V$	[1]				
		I _C = -500 mA		200	350	-	
		$I_{\rm C} = -1$ A		200	320	-	
		$I_{\rm C} = -2$ A		150	240	-	
		$I_{\rm C} = -4$ A		60	100	-	
V _{CEsat}	collector-emitter		[1]				
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}$		-	-110	-165	mV
		$I_{C} = -1 \text{ A}; I_{B} = -10 \text{ mA}$		-	-160	-240	mV
		$I_{C} = -2 \text{ A}; I_{B} = -40 \text{ mA}$		-	-200	-300	mV
		$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$		-	-230	-345	mV
	$I_{C} = -4 \text{ A}; I_{B} = -200 \text{ mA}$		-	-270	-400	mV	
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$	<u>[1]</u>	-	58	86	mΩ
V _{BEsat}	base-emitter	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}$	[1]	-	-0.78	-0.9	V
	saturation voltage	$I_{\rm C} = -4$ A; $I_{\rm B} = -400$ mA	[1]	-	-1.02	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	<u>[1]</u>	-	-0.81	-0.9	V
t _d	delay time	V _{CC} = -12.5 V;		-	30	-	ns
t _r	rise time	$I_{\rm C} = -1$ A; $I_{\rm Bon} = -0.05$ A;		-	60	-	ns
t _{on}	turn-on time	$I_{Boff} = 0.05 \text{ A}$		-	90	-	ns
t _s	storage time			-	140	-	ns
t _f	fall time			-	80	-	ns
t _{off}	turn-off time			-	220	-	ns
f⊤	transition frequency	$V_{CE} = -10 V;$ $I_{C} = -100 mA;$ f = 100 MHz		-	115	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz		-	85	-	pF

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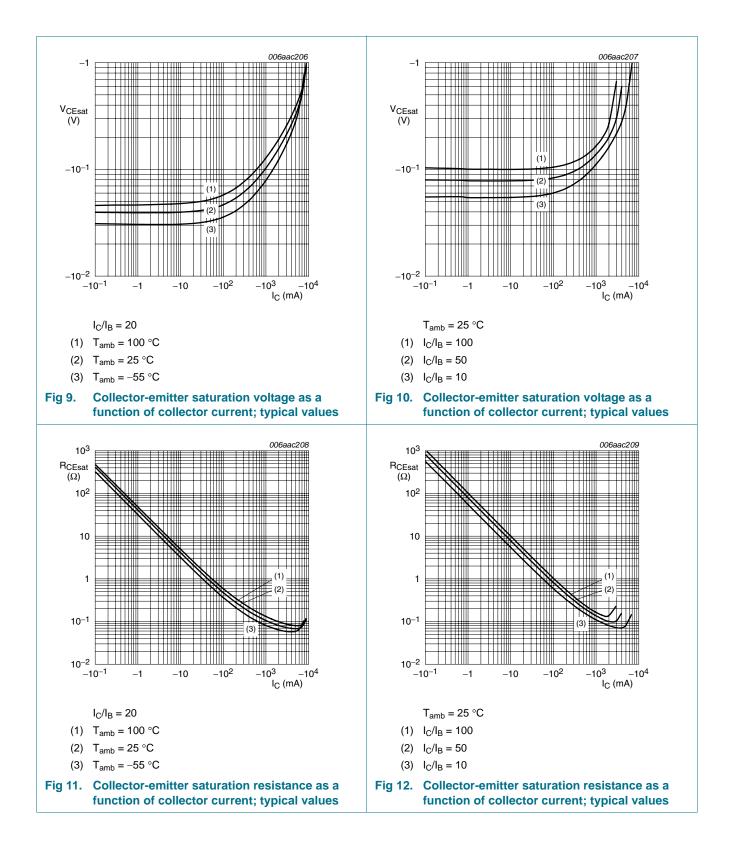
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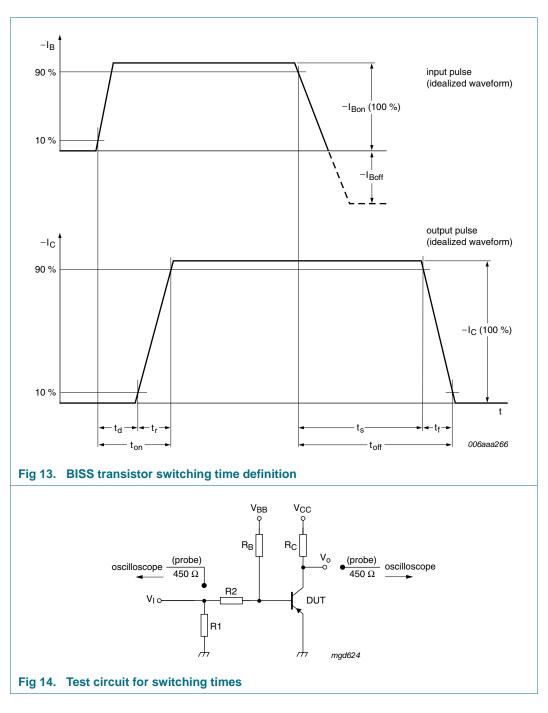
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8. Test information



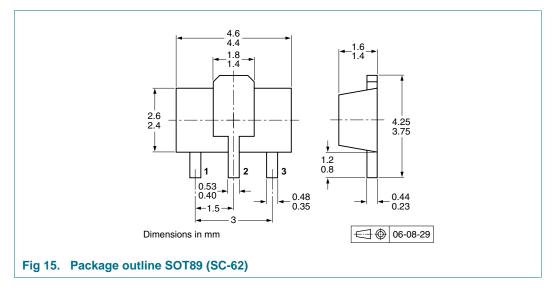
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

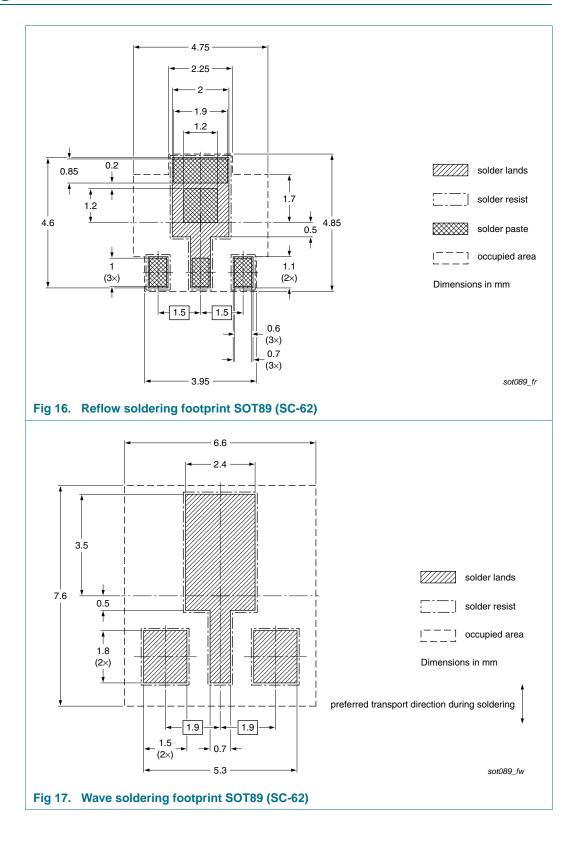
Type number	Package	Description		Packing quantity	
				3000	10000
PBSS4032PX	SOT89	8 mm pitch, 12 mm tape and reel; T1	[2]	-115	-135
		8 mm pitch, 12 mm tape and reel; T3	<u>[3]</u>	-120	-

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

- [2] T1: normal taping
- [3] T3: 90° rotated taping

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11. Soldering



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12. Revision history

Table 9. Rev	vision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4032PX_	1 20100401	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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